# Study of Polyaniline Polyacrylamide Composites by Positron Annihilation Technique

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**ABSTRACT:** Polyaniline doped with nonoxidizing Bronsted acids is recognized as a conducting material, as its electrical conductivity changes with percentage of doping. In the present work, different percentages of doped polyaniline were blended with polyacrylamide and their electrical conductivities as well as the positron annihilation lifetimes were measured. Analysis of data yielded three lifetime components. It was observed that the value of the short lifetime component remained constant for doping concentration, whereas that of the intermediate component  $\tau_2$  decreased. The relative intensity pertaining to  $\tau_2$ , however, increased with the increase in doped PANI concentration. © 2003 Wiley Periodicals, Inc. J Appl Polym Sci 89: 930–933, 2003

Key words: conducting polymer; polyaniline; composites

# INTRODUCTION

Polyaniline attracts considerable interest as a conducting material in its doped state (protonated PANI) due to the inexpensiveness of aniline and because protonated PANI can be easily synthesized. The wide range of associated electrical, electrochemical, and optical properties, coupled with excellent environmental stability of its emeraldine base and emeraldine salt form, make PANI potentially attractive for a variety of applications despite its brittleness and lack of processibility.<sup>1–4</sup>

To render this material useful, it is desirable to remove these drawbacks and make PANI processible. The present work is aimed at preparing a protonated composite PANI-based composite blend with another insulating polymer, polyacrylamide (PAM).

Positron annihilation lifetime (PAL) in a solid is determined not only by the electron density in its bulk and lattice structure but also by the existing defects such as cation vacancies that can trap positron and give rise to a longer lifetime component.<sup>5,6</sup> Peng et al.<sup>7</sup> correlated positron annihilation data with the conductivity obtained for different protonation levels in PANI. The present work is aimed at investigating the positron lifetimes as a function of doping concentration of protonated PANI in the blend.

### EXPERIMENTAL

# Materials

For synthesis of protonated PANI on the PAM base, we used PAM (BDH, MW 5,000,000), aniline (E. Merck), ammonium peroxydisulphate (E. Merck, Bombay, India), and hydrochloric acid (International Chemicals, Calcutta, India).

PAM (2 g) was dissolved in 200 ml water; ammonium peroxydisulphate (aniline : oxidant = 1 : 1.5) was added and thoroughly mixed. PAM films were cast on previously weighed glass plates and dried under vacuum at 50°C for 48 h until they attained constant weight. These films were exposed to HCl and then to aniline vapor and finally dried at 75°C under vacuum to remove excess aniline. The time of exposure over aniline varied to vary the polyaniline content of the composite. The films having low percentage of polyaniline were translucent but their opacity was seen to increase with an increase in the percentage of aniline.

# Positron annihilation setup

The PAL measurements at room temperature were carried out with a 4  $\mu$ Ci <sup>22</sup>Na positron source, sandwiched between two identical pellets of blended PANI. The sandwich was then placed in between two ultrafast BaF<sub>2</sub> scintillators (2.5 cm diameter and 2.5 cm thick) coupled to two XP2020Q photomultiplier tubes. These scintillation counters grafted into a slow–fast coincidence assembly constituted the PAL coincidence spectrometer. A time resolution of 190 ps was

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**Figure 1** Variation of conductivity as a function of doped PANI in different blend systems.

achieved in this setup. Not less than 0.5 million total coincidence counts were recorded in each of the spectra. The lifetime data were analyzed by using the computer program PATFIT-88.<sup>8</sup>

#### **RESULTS AND DISCUSSION**

Five different sets of samples having various percentages (viz., 1.3, 4.5, 8, 11.8, and 24) of protonated PANI blended with PAM were subjected to PAL studies. The resistivity of these samples were measured by employing the standard four-probe method. Figure 1 shows dependence of the results of conductivity on different blend compositions and Figure 2 shows the log of conductivity versus blend composition. It was seen that the conductivity increased from  $1.6 \times 10^{-8}$  to  $3.6 \times 10^{-5}$  mho up to 11.8% of protonated PANI, but attained a nearly constant value for higher percentages. The classical percolation theory<sup>9,10</sup> predicts a percolation threshold of 16% for spherical conducting particles dispersed in an insulating matrix. The value of percolation threshold ( $\simeq 12\%$ ) obtained in the present work was somewhat lower but was still large enough, indicating poor dispersion of PANI in the PAM matrix. Similar high values of percolation



**Figure 2** Variation of conductivity plotted on a log-scale as a function of doped PANI in different blend systems.



**Figure 3** Variation of conductivity as a function of temperature for the sample having 11.8% PANI in the blend.

threshold were not uncommon and were reported, for example, by Hotta et al.<sup>11</sup> for polythiophenes/polysty-rene composites.

That the degree of dispersion had an important influence on the percolation threshold is quite well known. Wang et al.<sup>12,13</sup> reported percolation threshold lower than 15% for polypyrole (PPy)/polyvinyl methyl ketone (PVMK) and PPy/PC systems and attributed this to better dispersion of PPy in the matrix polymer. The increased homogeneity observed for the PPy/PC system is due to H bonding between the carbonyl group of polycarbonate and the —NH group of polypyrrole. Similar results were observed for poly(*N*-methyl pyrrole)/polycarbonates and PPy/ poly (*n*-vinyl carbazole).<sup>14,15</sup> Lefrant and coworkers<sup>16</sup> obtained a low-percolation threshold for PPy/PVA composites and reported this to be due to good dispersion.

Many blend systems show a sharp percolation threshold. For comparison, we reproduced a figure (Fig. 4) from Machado et al.<sup>17</sup> along with our experimental results (curve F, Fig. 4). As can be seen, curve A for PA/low-density polyethylene (LDPE) blend shows a sharp percolation threshold at a very low volume fraction, which has been attributed to the fact that polyacetylene is incorporated only in the amorphous regions of the LDPE matrix. Curve C (Fig. 4) and curve E (Fig. 4) show broadened percolation at higher loadings. Machado et al. ascribed this behavior to the development of a nonequilibrium morphology. Curves B and D (Fig. 4) are for poly(methyl methacrylate) (PMMA)/graphite systems with PMMA matrices of different molecular weights. The percolation threshold observed for the present system (curve F, Fig. 4) is rather high and is due to poor dispersion of PANI in PAM, resulting in larger domains. This is consistent with the observations of Wang et al.,<sup>13</sup> who attributed lower percolation threshold to better dispersion of the conducting component in the matrix. The concentration dependence of PANI-PAM com-

PANI in different blend systems.

Figure 5 Variation of intensity  $I_2$  as a function of doped

mer. We optimally doped PANI and increased its percentage as a whole in the blend. This doped PANI has a constant amount of dislocations,<sup>7</sup> and hence,  $\tau_1$ remains constant. The  $\tau_2$  component originates from annihilation of positrons in the dislocation sites. However, as we increase the doped PANI in the blend, the dislocation density in the blend increases, and as a result,  $I_2$  increases. Figure 5 shows the variation of  $I_2$ and Figure 6 shows the variation of  $(I_2 + I_3)$  with the increase of doped PANI in the blend. From both figures, we see the  $I_2$  or  $(I_2 + I_3)$  attains saturation at about 12% of doped PANI in the blend. In Figure 2 we observe that the conductivity also attains saturation at the percolation percentage (11.8% of doped PANI in PAM). The doped PANI enters into the PAM structure up to 11.8% to form the conducting chain, and the remaining part does not contribute very much to conductivity. From the positron annihilation parameter, it is also seen that a small contribution has come from this excess portion of doped PANI in PAM.

From the experimental lifetime data, the bulk lifetime,  $\tau_{B'}$  using the simple two-state trapping model,<sup>23</sup> is calculated,

$$\tau_{B} = \frac{(I_{1} + I_{2})}{\left[\left(\frac{I_{1}}{\tau_{1}}\right) + \left(\frac{I_{2}}{\tau_{2}}\right)\right]}$$
(2)

Figure 7 shows the variation of  $\tau_B$  with the percentage of protonated PANI in PAM where  $\tau_B$  is seen to decrease as the percentage of protonated PANI in

**Figure 6** Variation of intensity  $(I_2 + I_3)$  as a function of doped PANI in different blend systems.

10

% OF PANI IN BLEND

20

INTENSITY I2+ I3(%)

65

55



posites observed conforms to the model of phasesegregated metallic domains (PANI) in an insulating matrix (PAM) proposed recently.<sup>18</sup>

The temperature dependence of PANI–PAM blends are shown in Figure 3 and follows the relation<sup>19</sup>

$$\sigma(T) = \sigma_0 \exp[(T_0/T)^{\gamma}] \tag{1}$$

with  $\gamma = 1/4$  and corresponds to variable range-hopping mode of transport among exponentially localized states. This is in agreement with the report of Salaneck et al.<sup>20</sup> showing that the conduction mechanism of PANI conforms to variable range-hopping mode.

Each PAL spectra of the PANI–PAM blends was resolved into three components; the short component,  $\tau_1$ , is due to the free annihilation of the positron<sup>21,22</sup> and the intermediate component,  $\tau_2$ , is due to the partial trapping of positrons at the vacancy defects. The longer third component,  $\tau_3$ , having values lying between 1.3 and 2 ns, is ascribed to the pick-off component of the ortho-positronium triplet.<sup>6</sup>

In the present experiment,  $\tau_1$  is found to remain constant (145 ps) but  $\tau_2$  decreases from 400 to 370 ps for an increase in doping of protonated PANI in the blend. The longest third component is ascribed to positronium formation and subsequent ortho- to paraconversion in the large voids in the blend system. The relative intensity of the  $\tau_3$  component is rather large (10–13%).

The intensity of the intermediate lifetime component  $I_2$  needs be given special attention here because the values of  $I_2$  are related to the level of protonation in PANI<sup>7</sup> that controls the conductivity in this poly-







**Figure 7** Variation of bulk lifetime  $\tau_{\rm B}$  as a function of doped PANI in different blend systems.

PAM increases up to the percolation percentage, above which  $\tau_B$  becomes nearly constant.

### CONCLUSION

In conclusion, the present article attempts to correlate the positron annihilation lifetime spectra with the composition of the PANI–PAM blend. It is observed that the conductivity reaches the maximum value for 11.8% percolation percentage of doped PANI in PAM and attains saturation for the higher percentage. Our main objective was to understand this effect by analyzing the positron annihilation parameters. While doing so, we found that the intensity of the intermediate positron lifetime component I<sub>2</sub> and the bulk lifetime,  $\tau_{B}$ , also attained nearly constant value above the percolation percentage.

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# References

1. DeSurville, R.; Jozefowiez, M.; Perichon, J.; Buvet, R. Electrochem Acta 1968, 13, 1451.

- 2. Genies, E. M.; Pierre, G.; Santier, C.; Tsintavis, C. Fr. Pat. 83,07,958
- Kobayashi, T.; Yoneyama, H.; Tamura, H. J Electroanal Chem 1984, 161, 281, 419.
- Zuo, F.; MacCall, R. P.; Ginder, J. M.; Roe, M. G.; Leng, J. M.; Epstein, A. J.; Astunias, G. E.; Ermer, S. P.; Ray, A.; MacDiarmid, A. G. Synth Met 1989, E445, 29.
- 5. Hautojarvi, P. Ed. Positron in Solids; Springer Verlag: Berlin, 1979.
- Sanyal, D.; Banerjee, D.; Bhattacharya, R.; Patra, S. K.; Chaudhuri, S. P.; Nandi Ganguly, B.; De, U. J Mater Sci 1996, 31, 3447.
- Peng, Z. L.; Li, S. Q.; Dai, Y. Q.; Wang, B.; Wang, S. J.; Liu, H.; Xie, H. Q. Synth Met 1994, 64, 33. [and refs. therein]
- Kirkegaard, P.; Pedersen, N. J.; Eldroup, M. Report of Riso National Lab; Riso-M-1989, 2740.
- 9. Zallen, R. The Physics of Amorphous Solids; Wiley; New York, 1983.
- 10. Stauffer, D. Introduction to Percolation Theory; Taylor and Francis; London, 1985.
- 11. Hotta, S.; Rughooputh, S. D. D.; Heeger, A. J. Synth. Metals 1987, 22, 79.
- 12. Wang, H. L.; Fernandez, J. E. Macromolecules 1992, 25, 6179.
- Wang, H. L.; Toparre, L.; Fernandez, J. E. Macromolecules 1990, 23, 1053.
- 14. Giessler, U.; Hallensleben, M. L.; Toparre, L. Ad Mater 1991, 3, 104.
- Giessler, U.; Hallensleben, M. L.; Toparre, L. Synth Metals 1991, 40, 239.
- Makhlouki, M.; Morsli, M.; Bonnet, A.; Conan, A.; Pron, A.; Lefrant, S. J Appl Polym Sci 1992, 44, 443.
- 17. Machado, J. M.; Karasz, F. E.; Lenz, R. W. Polymer 1988, 29, 1412.
- Ginder, J. M.; Richter, A. F.; MacDiarmid, A. G.; Epstein, A. J. Solid State Commun 1987, 63, 97.
- Mott, N. F.; Davies, E. A. Electronic Processes in Non Crystalline Material; Clarendon Press: Oxford, UK, 1979.
- Solanear, W. R.; Lunzbert, B.; Londstrom, I. Synth Met 1987, 21, 143.
- 21. Schaefer, H. E.; Forster, M. Mat Sci and Eng 1989, A109, 161.
- Weber, J. T.; Snead Jr., C. L.; Lynn, K. G. In Positron Annihilation, Ed., Jain, P. C.; Singru, R. M.; Gopinathan, K. P. World Scientific, Singapore, 1985.
- 23. Seeger, A. J Phys F 1973, 3, 248.